

JLCD200B120R34E7DN

L34 module with GEN7 IGBT and emitter controlled diode

Features

- Electrical features
 - V_{CES} = 1200 V
 - $-I_{C \text{ nom}} = 200 \text{ A} / I_{CRM} = 400 \text{ A}$
 - V_{CEsat} with positive temperature coefficient
 - 10µs short circuit capability
- Mechanical features
 - Standard housing
 - 2.5 kV AC 1 min insulation
 - High creepage and clearance distances
 - Isolated base plate

Typical Applications

- Inverters
- UPS (Uninterruptible Power Supplies)
- Motor Control

JINLAN

= Company Name

JLCD200B120R34E7DN = Specific Device Code

YYWW

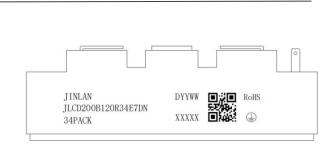
= Year and Work Week Code

XXXXX

= Serial Number

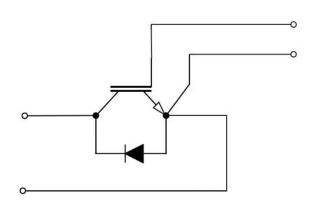
QR code

= Custom Assembly Information



L34

Description





Package Insulation coordination

Symbol	Parameter	Note or test condition	Values	Unit
Visol	Isolation test voltage	RMS,f=50Hz,t=60s	2.5	kV
d _{creep}	Creepage distance	terminal to heatsink	17.0	mm
d_{creep}	Creepage distance	terminal to terminal	20.0	mm
d _{clear}	Clearance	terminal to heatsink	17.0	mm
d _{clear}	Clearance	terminal to terminal	9.5	mm
0.77	Comparative tracking index		- 475	
СТІ	(electrical)		≥175	

Package Characteristic values

Symbol				Values			
Symbol	Description	Note or test co	Note or test condition		Тур.	Max.	Unit
L _{sCE}	Stray Inductance				30		nH
R _{CC'+EE'}	Module Lead Resistance, Terminal to Chip	T _C =25°C, per switch			0.75		mΩ
T_{stg}	Storage temperature			-40		125	°C
M	Mounting torque for module mounting	-Mounting according to valid application note	M5, Screw	2.5		5.0	Nm
М	Terminal connection torque	-Mounting according to valid application note	M6, Screw	3.0		5.0	Nm
G	Weight				150		g



IGBT

Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

Symbol	Description	Note or test condition	Value	Unit
V_{CES}	Collector-Emitter Voltage	T _{vj} = 25 °C	1200	V
I _{CDC}	Continuous Collector Current @ Tc = 80°C (T _{JMAX} = 175°C)		200	Α
Іскм	Repetitive peak collector current	Peak Collector Current@ tp=1ms	400	А
P _{tot}	Total power dissipation	$T_C = 25^{\circ}C, T_{vj \text{ max}} = 175^{\circ}C$	880	w
V _{GES}	Gate-emitter peak voltage		±30	V

Characteristics (Tc = 25°C unless otherwise noted)

		Test Condition			Rating		
Symbol	Parameter			Min	Тур	Max	Unit
	Collector-Emitter Saturation Voltage	IC=200A	Tj=25°C		1.40	2.20	V
$V_{CE(sat)}$	Johnson Elimion Calairanon Voltage	VGE=15V	Tj=150°C		1.60		
$V_{\text{GE(TH)}}$	Gate-Emitter Threshold Voltage	$I_C = 5\text{mA}, V_C$	_{SE} = V _{GE}	5.0	6.0	7.0	V
Ices	Collector-Emitter Cutoff Current	V _{GE} =0V,V _{CE} =120	0V,T _{vj} = 25°C			500	uA
I _{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20V$, $V_{CE} = 0 V$, $T_{vj} = 25^{\circ}C$				+/-200	nA
R _{Gint}	Internal Gate Resistance	T _{vj} = 25 °C			3.37		Ω
C_ies	Input Capacitance	V _{CE} =30V,V _{GE} =0V, f=1MHz,T _{vj} = 25°C			31.9		
C_oes	Output Capacitance				0.787		nF
C _{res}	Reverse Transfer Capacitance				0.158		
Qg	Total Gate Charge	V _{CC} =960V, I _C =200A, V _{GE} =15V,T _{Vj} = 25°C			1.06		uC
$t_{\text{d}(\text{ON})}$	Turn-on Delay Time				387		
t _r	Rise Time	V_{CE} =600V, I_{C} =200A, V_{GE} =15/-5V, R_{g} =25 Ω Inductive Load			262		
$t_{\text{d(OFF)}}$	Turn-Off Delay Time				1307		ns
t _f	Fall Time				193		
E _{on}	Turn-On Switching Loss				17.931		1
E _{off}	Turn-Off Switching Loss				9.031		mJ



Ets	Total Switching Loss		-	26.961	-	
I _{C(SC)}	Short circuit collector curren	V_{GE} =15V, V_{CC} =600V, t_{SC} ≤10us, T_{vj} ≤150°C		1000		Α
R _{thJC}	Thermal resistance,junction to case	per IGBT		0.15		K/W
T _{vj op}	Temperature under switching conditions		-40		175 ¹⁾	$^{\circ}$

 $^{^{1)}}T_{\nu j\,op}$ > 150 $^{\circ}{\rm C}$ is only allowed for operation at overload conditions.

Diode

Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

	,			
Symbol	Description	Note or test condition	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	T _{vj} = 25 °C	1200	٧
I _F	Continuous DC forward current		200	Α
I _{FRM}	Repetitive peak forward current	t _P = 1 ms	400	А

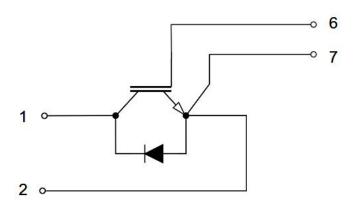
Characteristics (Tc = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Rating			Units
Symbol		rest Conditions	Min.	Тур.	Max.	Oille
VF	Diode Forward Voltage	I _F =150A		1.6	2.6	V
T _{rr}	Reverse Recovery Time			175		ns
I _{RRM}	Diode Peak Reverse Recovery Current	V _{CE} =600V,I _F =200A, V _{GE} =15/-5V		27		А
Qrr	Reverse Recovery Charge	$R_g=25\Omega$		1.24		uC
Erec	Reverse Recovery Energy			1.23		mJ
RthJC	Thermal resistance,junction to case	per Diode		0.3		K/W
T _{vj op}	Temperature under switching conditions		-40		175 ²⁾	$^{\circ}$

 $^{^{2)}}T_{\nu j\,op}$ > 150 $^{\circ}\mathrm{C}$ is only allowed for operation at overload conditions.

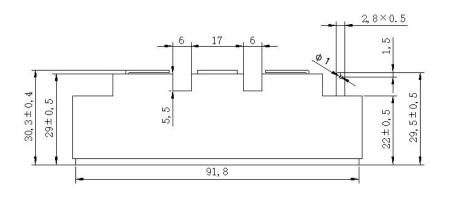
Circuit Diagram

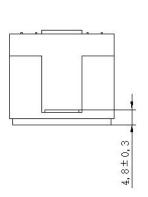


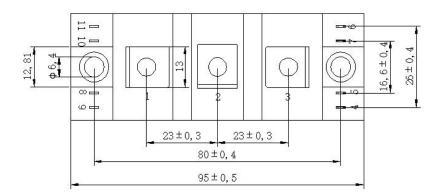


Package Dimensions

Dimensions in Millimeters









REVISION HISTORY

Document version	Date of release	Description of changes
Rev.00	2025-1-7	Preview
Rev.01	2025-3-18	Qg,Rg,Cies,Coes,Cres value updated



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